

产品概览

FFSH10120ADN: SiC Diode, 1200V, 10A, TO-247-3, Common Cathode

欲看完整文档，请参阅数据表。

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability to silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.

特性

- Max Junction Temperature 175 °C
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery / No Forward Recovery

应用

- PFC
- Industrial Power
- Solar
- EV Charger
- UPS

器件电气规格

| 产品 | Compliance | Status | Device Grade | Configuration | V_{RRM} (V) | $I_{F(ave)}$ (A) | V_F (Max) | I_{FSM} (A) | I_R (Max) (μA) | Package Type |
|-------------------|------------------------|--------|--------------|---------------|---------------|------------------|-------------|---------------|-------------------------|--------------|
| FFSH10120ADN-F155 | Pb-free Halide free | NEW | | | | | | | | TO-247-3 |

欲了解更多信息，请联系您当地的销售支援 www.onsemi.cn。

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